TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC74HC283AP,TC74HC283AF,TC74HC283AFN

#### 4-Bit Binary Full Adder

The TC74HC283A is a high speed CMOS 4-BIT BINARY FULL ADDER fabricated with silicon gate C<sup>2</sup>MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

Sum  $(\Sigma)$  outputs are provided for each bit and a resultant carry (C4) is obtained from the fourth bit.

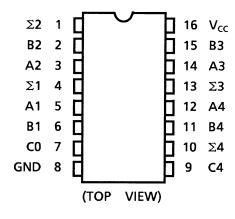
This adder features full internal look-ahead across all four bits.  $A4 \times n$  bit binary adder is easily built up by cascading the HC283A without any additional logic.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

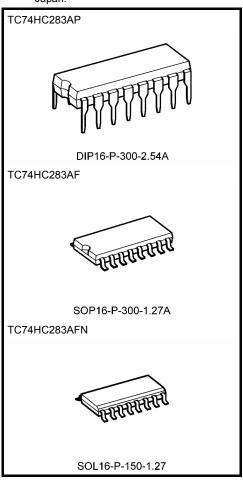
#### **Features**

- High speed:  $t_{pd} = 17 \text{ ns (typ.)}$  at  $V_{CC} = 5 \text{ V}$
- Low power dissipation:  $I_{\rm CC}$  = 4  $\mu A$  (max) at Ta = 25°C
- High noise immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (min)
- Output drive capability: 10 LSTTL loads
- Symmetrical output impedance: |IOH| = IOL = 4 mA (min)
- Balanced propagation delays:  $t_{pLH} \approx t_{pHL}$
- Wide operating voltage range: VCC (opr) = 2 to 6 V
- Pin and function compatible with 74LS283

#### **Pin Assignment**



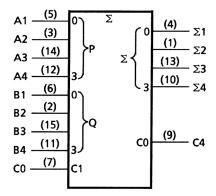
Note: xxxFN (JEDEC SOP) is not available in Japan.



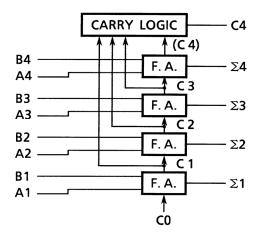
Weight

DIP16-P-300-2.54A : 1.00 g (typ.) SOP16-P-300-1.27A : 0.18 g (typ.) SOL16-P-150-1.27 : 0.13 g (typ.)

## **IEC Logic Symbol**



### **Block Diagram**

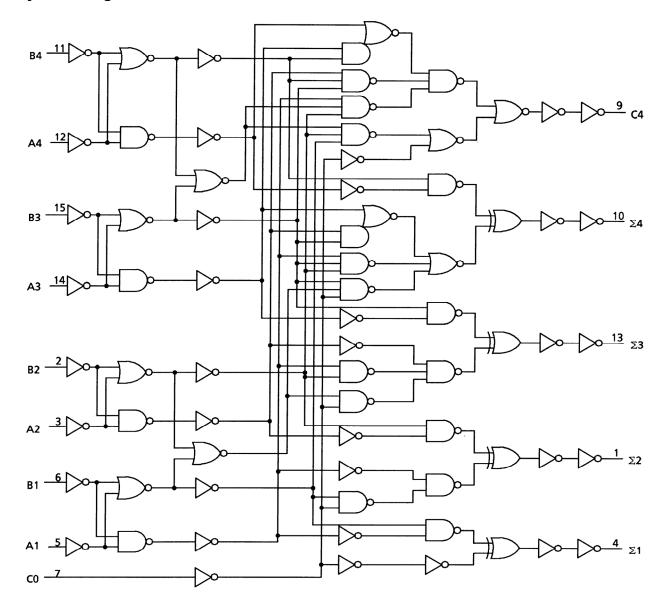


### Truth Table (1 bit)

	Input	Outputs			
Bn	An	Cn – 1	Σn	Cn	
L	L	L	L	L	
L	L	Н	Н	L	
L	Н	L	Н	L	
L	Н	Н	L	Н	
Н	L	L	Н	L	
Н	L	Н	L	Н	
Н	Н	L	L	Н	
Н	Н	Н	Н	Н	

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## **System Diagram**



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### **Absolute Maximum Ratings (Note 1)**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	–0.5 to 7	V
DC input voltage	V <sub>IN</sub>	-0.5 to V <sub>CC</sub> + 0.5	V
DC output voltage	V <sub>OUT</sub>	−0.5 to V <sub>CC</sub> + 0.5	٧
Input diode current	I <sub>IK</sub>	±20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V <sub>CC</sub> /ground current	Icc	±50	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP)	mW
Storage temperature	T <sub>stg</sub>	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to  $65^{\circ}C$ . From Ta = 65 to  $85^{\circ}C$  a derating factor of -10 mW/°C shall be applied until 300 mW.

### **Operating Ranges (Note)**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	2 to 6	V
Input voltage	V <sub>IN</sub>	0 to V <sub>CC</sub>	V
Output voltage	V <sub>OUT</sub>	0 to V <sub>CC</sub>	٧
Operating temperature	T <sub>opr</sub>	−40 to 85	°C
		0 to 1000 (V <sub>CC</sub> = 2.0 V)	
Input rise and fall time	t <sub>r</sub> , t <sub>f</sub>	0 to 500 (V <sub>CC</sub> = 4.5 V)	ns
		0 to 400 (V <sub>CC</sub> = 6.0 V)	

Note: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.



### **Electrical Characteristics**

#### **DC Characteristics**

Characteristics Symbol		Test Condition $V_{CC}\left(V\right)$		Ta = 25°C			Ta = -40 to 85°C		Unit	
				V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	
		_		2.0	1.50	_	_	1.50	_	
High-level input voltage	V <sub>IH</sub>			4.5	3.15	_	_	3.15	_	V
Ţ.				6.0	4.20	—	_	4.20	_	
		_		2.0	_	_	0.50	_	0.50	
Low-level input voltage	$V_{IL}$			4.5	_	_	1.35	_	1.35	V
Ţ.				6.0		—	1.80	_	1.80	
	Vон	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>		2.0	1.9	2.0	_	1.9	_	
			$I_{OH} = -20 \mu A$	4.5	4.4	4.5	_	4.4	_	
High-level output voltage				6.0	5.9	6.0	_	5.9	_	V
			$I_{OH} = -4 \text{ mA}$	4.5	4.18	4.31	_	4.13	_	
			$I_{OH} = -5.2 \text{ mA}$	6.0	5.68	5.80		5.63	_	
	V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>		2.0		0.0	0.1	_	0.1	
			$I_{OL} = 20 \mu A$	4.5	_	0.0	0.1	_	0.1	
Low-level output voltage				6.0		0.0	0.1		0.1	V
			I <sub>OL</sub> = 4 mA	4.5		0.17	0.26	_	0.33	
			$I_{OL} = 5.2 \text{ mA}$	6.0	_	0.18	0.26	_	0.33	
Input leakage current	I <sub>IN</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND		6.0		_	±0.1		±1.0	μА
Quiescent supply current	I <sub>CC</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND		6.0	_	_	4.0		40.0	μА

### AC Characteristics ( $C_L = 15 \text{ pF}$ , $V_{CC} = 5 \text{ V}$ , $Ta = 25^{\circ}\text{C}$ , input: $t_r = t_f = 6 \text{ ns}$ )

Characteristics	Symbol	Test Condition		Тур.	Max	Unit
Output transition time	t <sub>TLH</sub>			4	8	ns
Output transition time	t <sub>THL</sub>	_	_	4	8	115
Propagation delay time	t <sub>pLH</sub>			17	00	
(C0-Σn)	t <sub>pHL</sub>	_	_	17	26	ns
Propagation delay time	t <sub>pLH</sub>			17	26	ns
(C0-C4)	t <sub>pHL</sub>	_	_	17	20	115
Propagation delay time	t <sub>pLH</sub>			23	37	20
(An, Bn- $\Sigma$ n)	t <sub>pHL</sub>	_	_	23	31	ns
Propagation delay time	t <sub>pLH</sub>			21	34	20
(An, Bn-C4)	t <sub>pHL</sub>			<u> </u>	34	ns

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AC Characteristics (CL = 50 pF, input:  $t_r = t_f = 6 \text{ ns}$ )

Characteristics	Symbol	Symbol Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit
<b>5</b> , <b>5</b>	,		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	
Output transition time	t <sub>TLH</sub> t <sub>THL</sub>	_	2.0 4.5 6.0		30 8 7	75 15 13		95 19 16	ns
Propagation delay time $(C0-\Sigma n)$	<sup>t</sup> pLH <sup>t</sup> pHL	_	2.0 4.5 6.0	_ _ _	60 20 17	150 30 26	_ _ _	190 38 32	ns
Propagation delay time (C0-C4)	t <sub>p</sub> LH t <sub>p</sub> HL	_	2.0 4.5 6.0	_ _ _	60 20 17	150 30 26	_ _ _	190 38 32	ns
Propagation delay time (An, Bn-Σn)	<sup>t</sup> pLH <sup>t</sup> pHL	_	2.0 4.5 6.0	_ _ _	95 27 22	210 42 36	_ _ _	265 53 45	ns
Propagation delay time (An, Bn-C4)	<sup>t</sup> pLH <sup>t</sup> pHL	_	2.0 4.5 6.0	_ _ _	80 25 20	195 39 33	_ _ _	245 49 42	ns
Input capacitance	C <sub>IN</sub>	_	•	_	5	10	_	10	pF
Power dissipation capacitance	C <sub>PD</sub> (Note)	_		_	126	_	_	_	pF

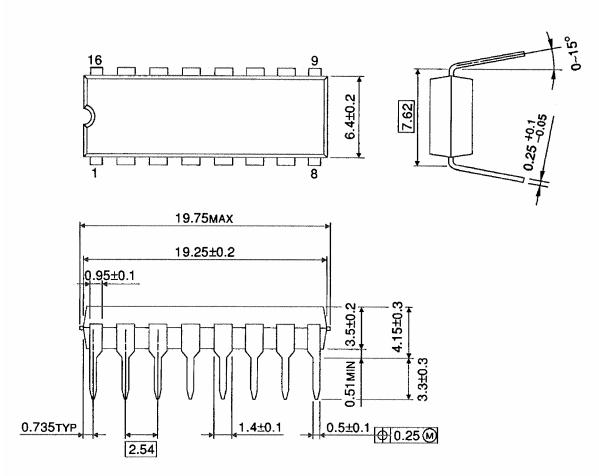
Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC}$$
 (opr) =  $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

## **Package Dimensions**

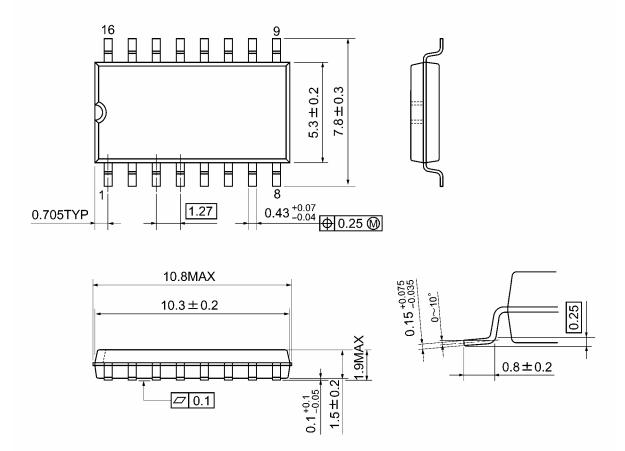
DIP16-P-300-2.54A Unit: mm



Weight: 1.00 g (typ.)

## **Package Dimensions**

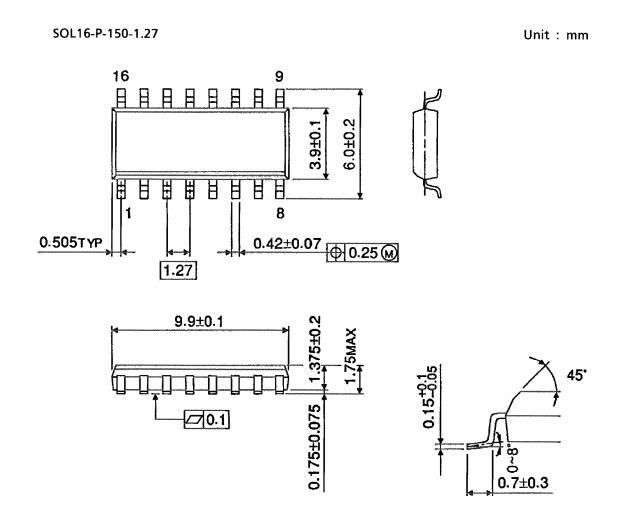
SOP16-P-300-1.27A Unit: mm



Weight: 0.18 g (typ.)



## **Package Dimensions (Note)**



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Note: This package is not available in Japan.

Weight: 0.13 g (typ.)

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20070701-EN GENERAL

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